

## **TSM2306**

### 30V N-Channel MOSFET

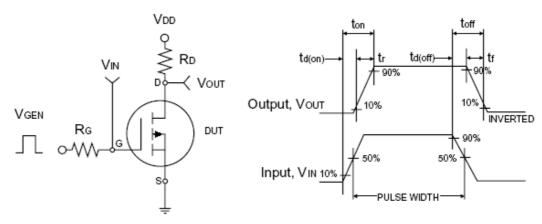


**Electrical Specifications** (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit			
Static									
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV <sub>DSS</sub>	30			V			
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	$V_{GS(TH)}$	1		3	V			
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I <sub>GSS</sub>			±100	nA			
Zero Gate Voltage Drain Current	$V_{DS} = 30V, V_{GS} = 0V$	I <sub>DSS</sub>			1.0	μΑ			
On-State Drain Current	$V_{DS} \ge 4.5 V, V_{GS} = 10 V$	I <sub>D(ON)</sub>	6			Α			
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 3.5A$	R <sub>DS(ON)</sub>		46	57	mΩ			
	$V_{GS} = 4.5V, I_D = 2.8A$			70	94				
Forward Transconductance	$V_{DS} = 15V, I_{D} = 3.5A$	$g_{fs}$	1	11		S			
Diode Forward Voltage	$I_S = 1.7A, V_{GS} = 0V$	$V_{SD}$	1	-1	1.2	V			
Dynamic <sup>b</sup>									
Total Gate Charge	\\	$Q_g$		4.2	7	nC			
Gate-Source Charge	$V_{DS} = 15V, I_D = 3.5A,$	$Q_{gs}$		1.9					
Gate-Drain Charge	V <sub>GS</sub> = 10V	$Q_{gd}$		1.35					
Input Capacitance	\/ 45\/ \/ 0\/	C <sub>iss</sub>	-	555		pF			
Output Capacitance	$V_{DS} = 15V, V_{GS} = 0V,$	C <sub>oss</sub>	1	120					
Reverse Transfer Capacitance	f = 1.0MHz	$C_{rss}$		60					
Switching <sup>c</sup>									
Turn-On Delay Time	\/ 45\/ D 450	t <sub>d(on)</sub>		4.2	5.5	nS			
Turn-On Rise Time	$V_{DD} = 15V, R_{L} = 15\Omega,$	t <sub>r</sub>		19	25				
Turn-Off Delay Time	$I_D = 1A, V_{GEN} = 10V,$	t <sub>d(off)</sub>		13	17				
Turn-Off Fall Time	$R_G = 6\Omega$	t <sub>f</sub>		9	12				

#### Notes:

- a. pulse test: PW ≤300µS, duty cycle ≤2%
  b. For DESIGN AID ONLY, not subject to production testing.
  b. Switching time is essentially independent of operating temperature.



**Switching Test Circuit** 

Switchin Waveforms



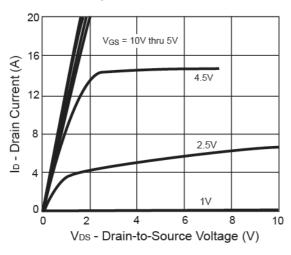
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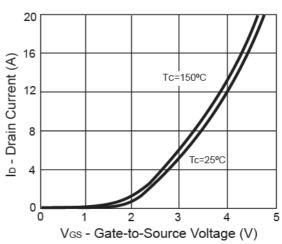


### Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

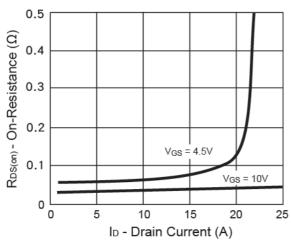
#### **Output Characteristics**



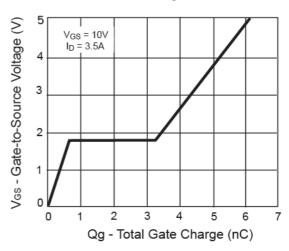
### **Transfer Characteristics**



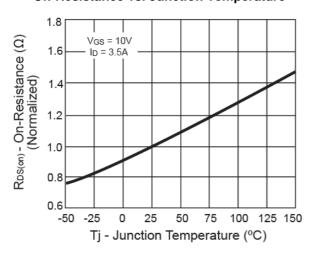
#### **On-Resistance vs. Drain Current**



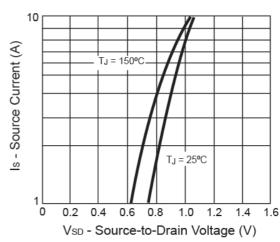
**Gate Charge** 



#### **On-Resistance vs. Junction Temperature**



Source-Drain Diode Forward Voltage





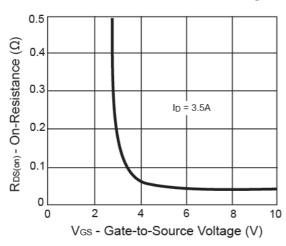
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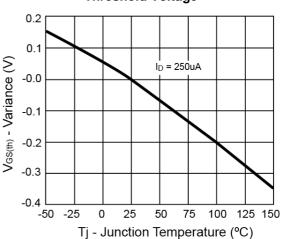


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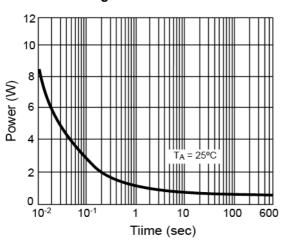
#### On-Resistance vs. Gate-Source Voltage



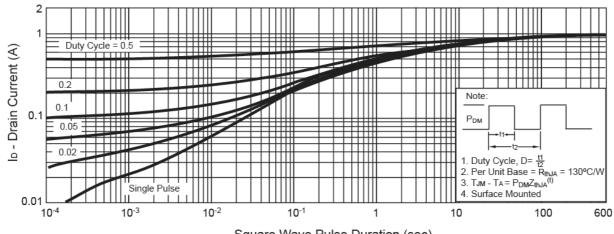
### Threshold Voltage



#### **Single Pulse Power**



#### Normalized Thermal Transient Impedance, Junction-to-Ambient



Square Wave Pulse Duration (sec)

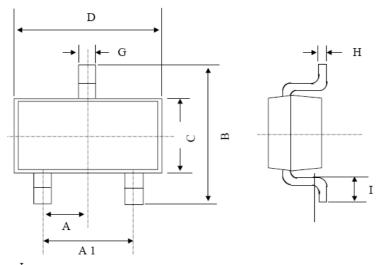




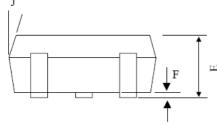


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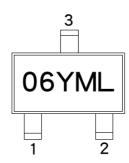
## **SOT-23 Mechanical Drawing**



SOT-23 DIMENSION							
DIM	MILLIM	ETERS	INCHES				
DIIVI	MIN	MAX	MIN	MAX.			
Α	0.95	BSC	0.037 BSC				
A1	1.9 [	BSC	0.074	BSC			
В	2.60	3.00	0.102	0.118			
С	1.40	1.70	0.055	0.067			
D	2.80	3.10	0.110	0.122			
E	1.00	1.30	0.039	0.051			
F	0.00	0.10	0.000	0.004			
G	0.35	0.50	0.014	0.020			
Н	0.10	0.20	0.004	0.008			
ı	0.30	0.60	0.012	0.024			
J	5°	10°	5°	10°			



# **Marking Diagram**



06 = Device Code

Y = Year Code

**M** = Month Code for Halogen Free Product

O =Jan P =Feb Q =Mar R =Apr

S =May T =Jun U =Jul V =Aug

W = Sep X = Oct Y = Nov Z = Dec

L = Lot Code



### TSM2306 30V N-Channel MOSFET

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